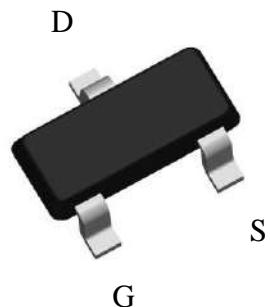


N-Channel Enhancement Mode MOSFET

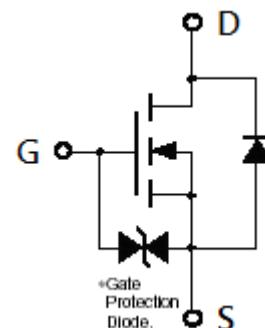
Description:

- Low voltage drive(2.5V drive) makes this device ideal for portable equipment.
- The MOSFET elements are independent, eliminating mutual interference.
- Mounting cost and area can be cut in half.
- High speed switching
- ESD protected device, HBM \geq 2kV
- Pb-free lead plating & halogen-free package

SOT-523



BVDSS		60V
ID@VGS=4.5V, TA=25°C		215mA
RDS(on)(TYP)	V_{GS}=4.5V, I_D=200mA	1.3Ω
	V_{GS}=2.5V, I_D=100mA	1.7Ω



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KWAK6-5	SOT-523 (Pb-free lead plating & halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	BVDSS	60	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	215	mA
Pulsed Drain Current	IDM	860 *1	
Total Power Dissipation	PD	150 *2	mW
ESD susceptibility	VESD	2000 *3	V
Operating Junction and Storage Temperature Range	Tj ; Tstg	-55~+150	°C

Note : *1. Pulse Width ≤ 10μs, Duty cycle ≤ 1%

*2. With each pin mounted on the recommended lands.

*3. Human body model, 1.5kΩ in series with 100pF

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient, max	*R _{θJA}	833	°C/W

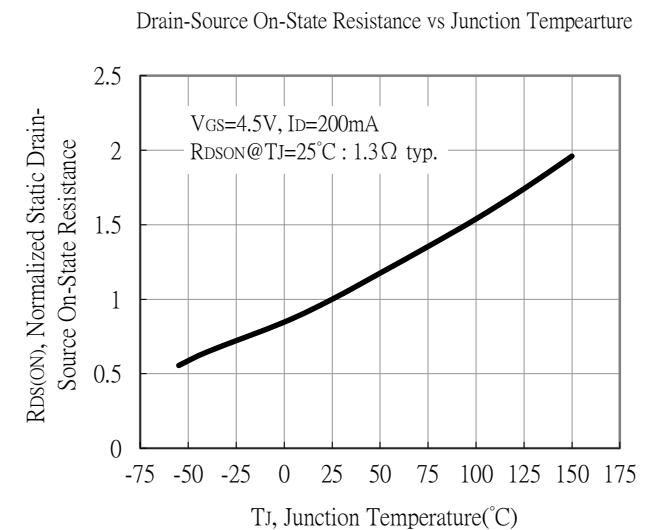
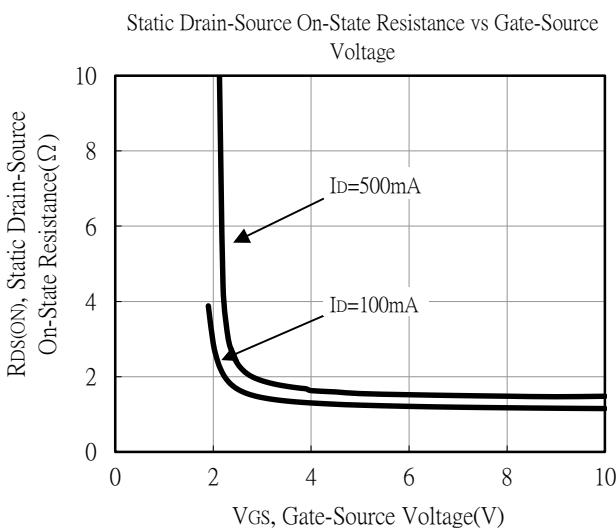
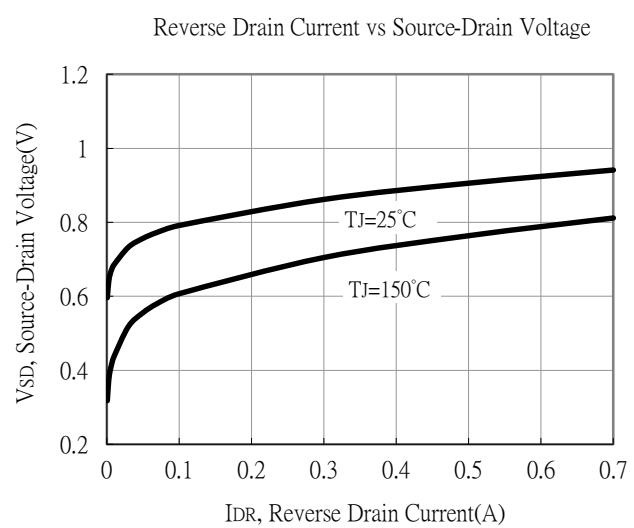
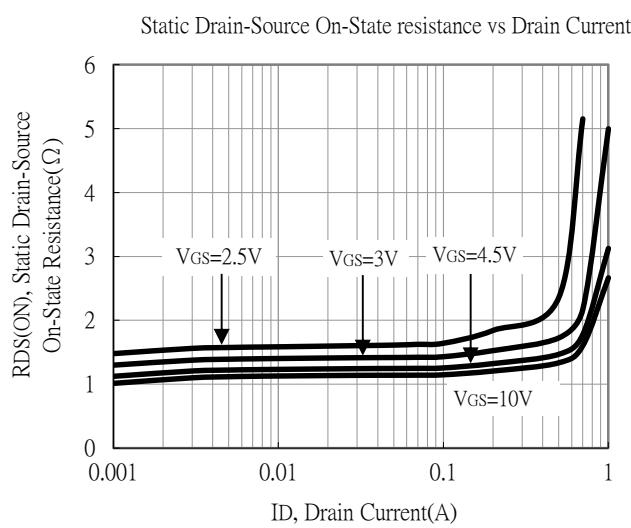
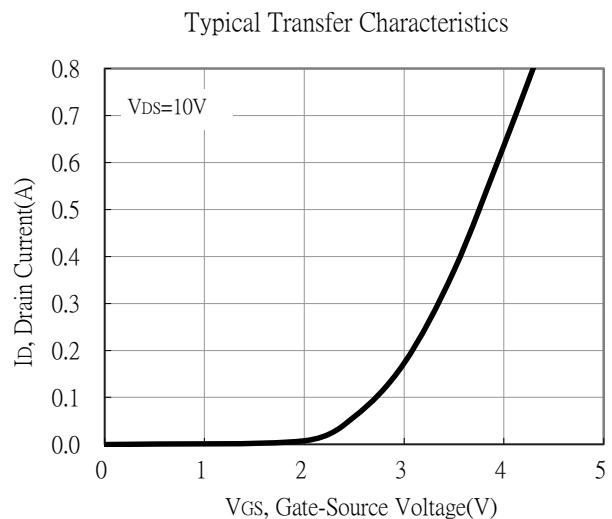
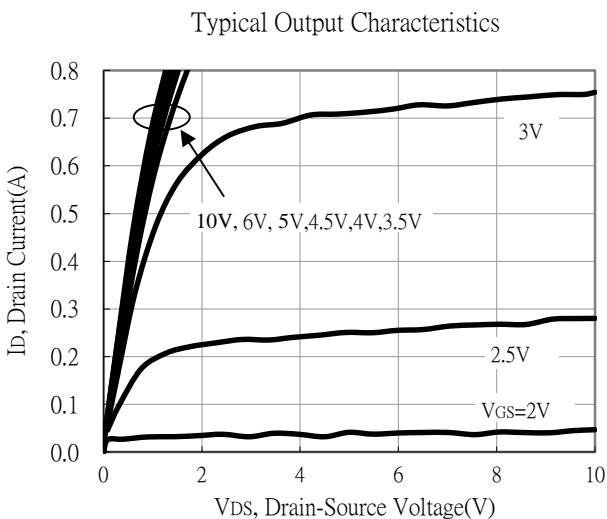
Note : With each pin mounted on the recommended lands.

Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions	
Static						
BVDSS	60	-	-	V	V _{GS} =0V, I _D =250μA	
V _{GS(th)}	0.5	-	1.5		I _D =250μA, V _{DS} =V _{GS}	
I _{GSS}	-	-	±10	μA	V _{GS} =±16V, V _{DS} =0V	
I _{DSS}	-	-	1		V _{DS} =60V, V _{GS} =0V	
R _{DS(ON)}	-	1.3	3	Ω	V _{GS} =4.5V, I _D =200mA	
	-	1.7	5.1		V _{GS} =2.5V, I _D =100mA	
G _{FS}	100	322	-	mS	V _{DS} =5V, I _D =100mA	
Dynamic						
C _{iss}	-	25.8	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz	
C _{oss}	-	8.6	-			
C _{rss}	-	7	-			
t _{d(on)}	-	3.1	-	ns	V _{DD} =30V, I _D =200mA, V _{GS} =10V, R _G =25Ω	
t _r	-	15.1	-			
t _{d(off)}	-	11.4	-			
t _f	-	18	-			
*Q _g	-	1.6	-	nC	V _{DS} =30V, I _D =0.5A, V _{GS} =10V	
*Q _{gs}	-	0.4	-			
*Q _{gd}	-	0.2	-			
R _g	-	3	-	Ω	f=1MHz	
Source-Drain Diode						
*V _{SD}	-	0.79	1.2	V	V _{GS} =0V, I _S =100mA	
*t _{rr}	-	8.3	-	ns	I _F =0.5A, dI _F /dt=100A/μs	
*Q _{rr}	-	2.7	-	nC		

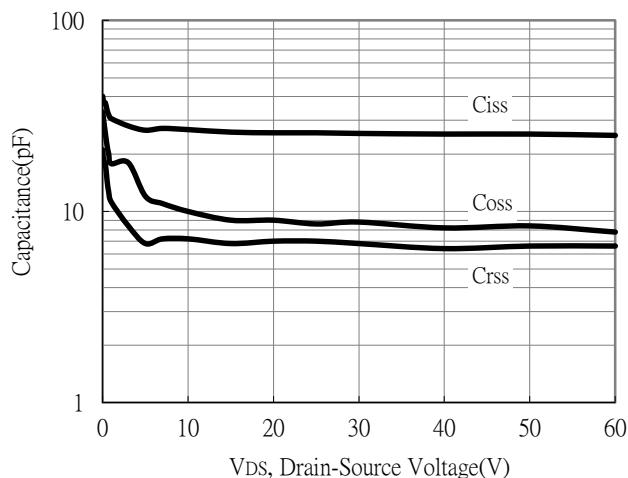
*Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Typical Characteristics

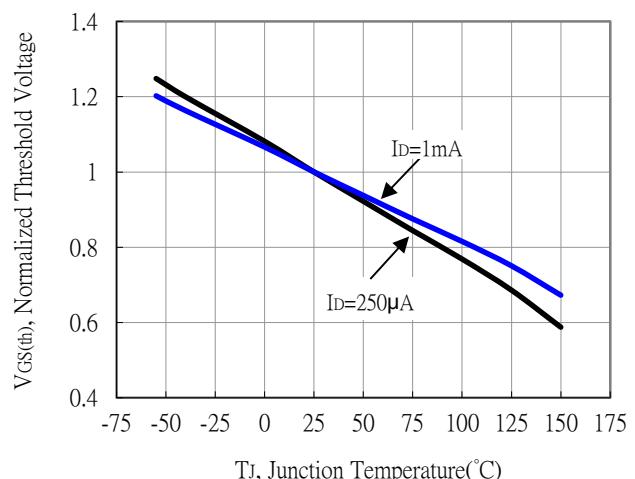


Typical Characteristics(Cont.)

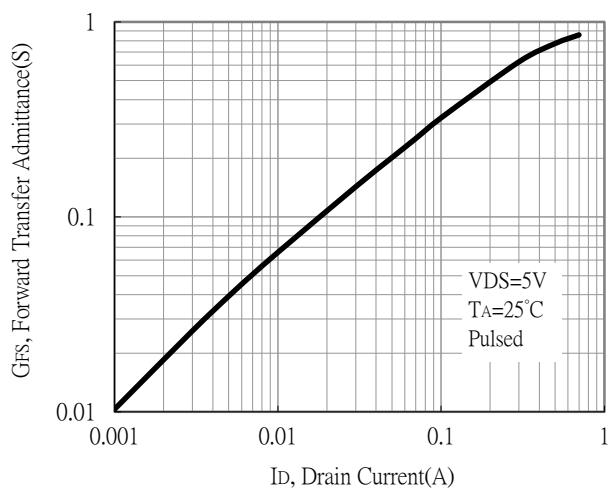
Capacitance vs Drain-to-Source Voltage



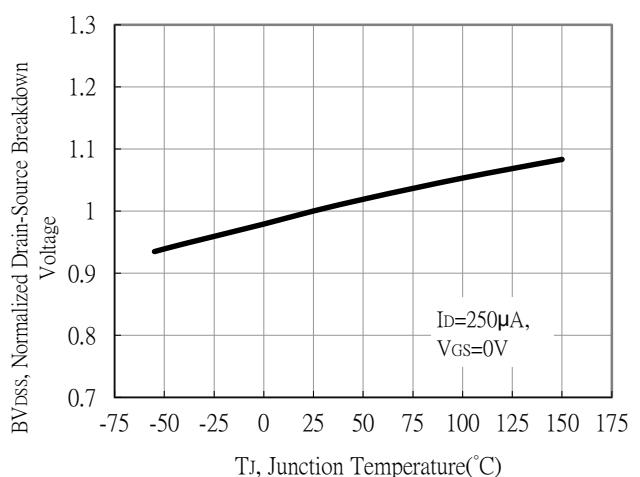
Threshold Voltage vs Junction Temperature



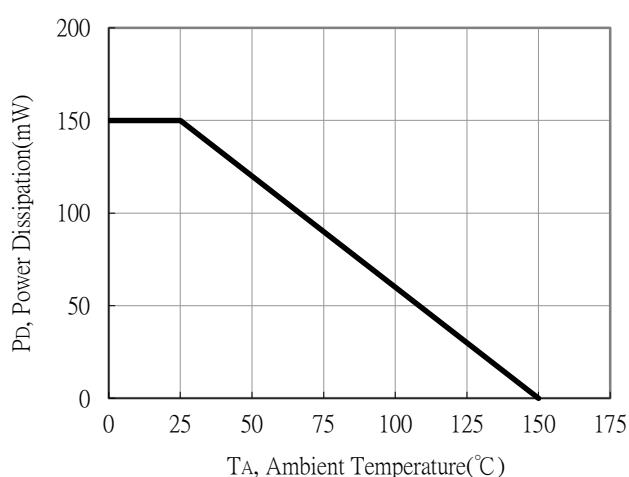
Forward Transfer Admittance vs Drain Current



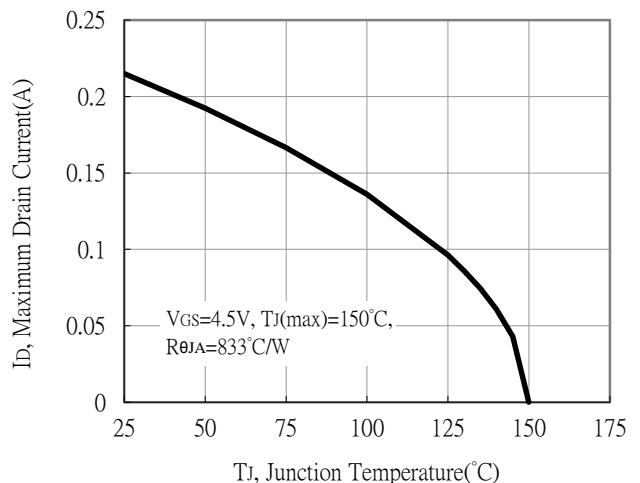
Breakdown Voltage vs Ambient Temperature



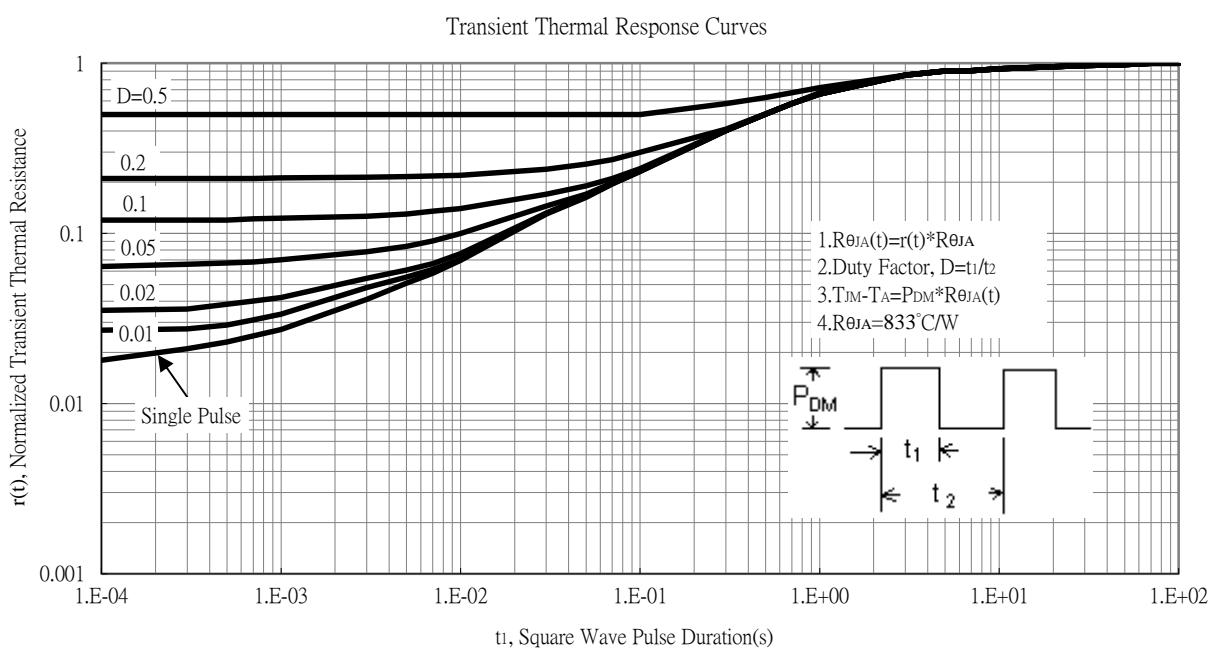
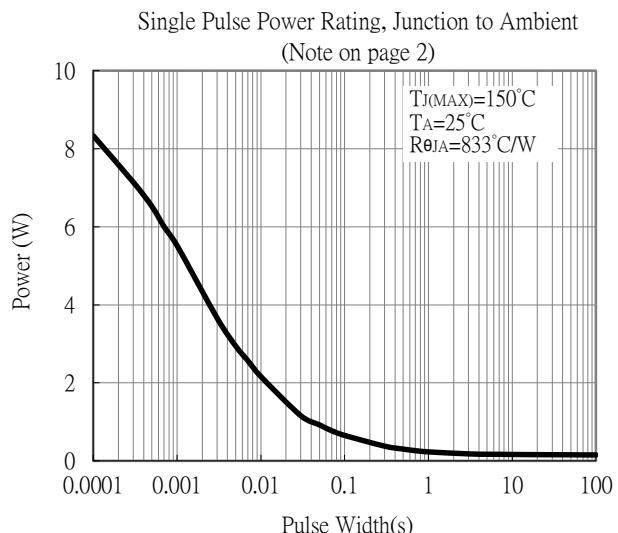
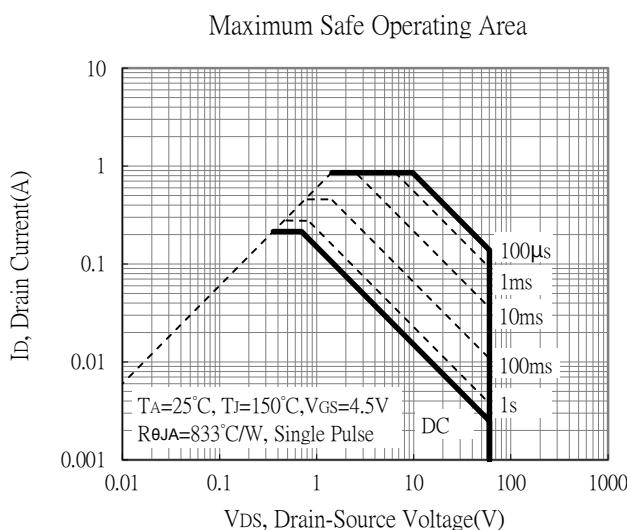
Power Derating Curve



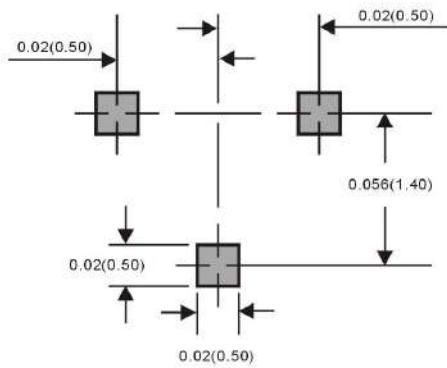
Maximum Drain Current vs Junction Temperature



Typical Characteristics(Cont.)

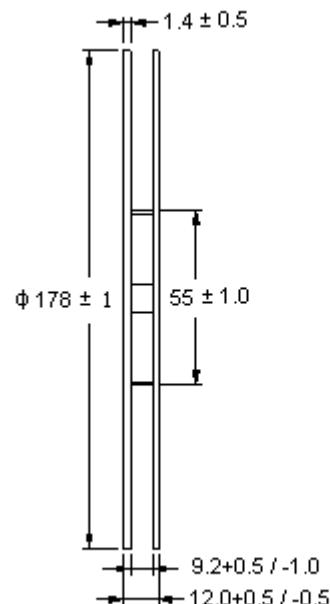
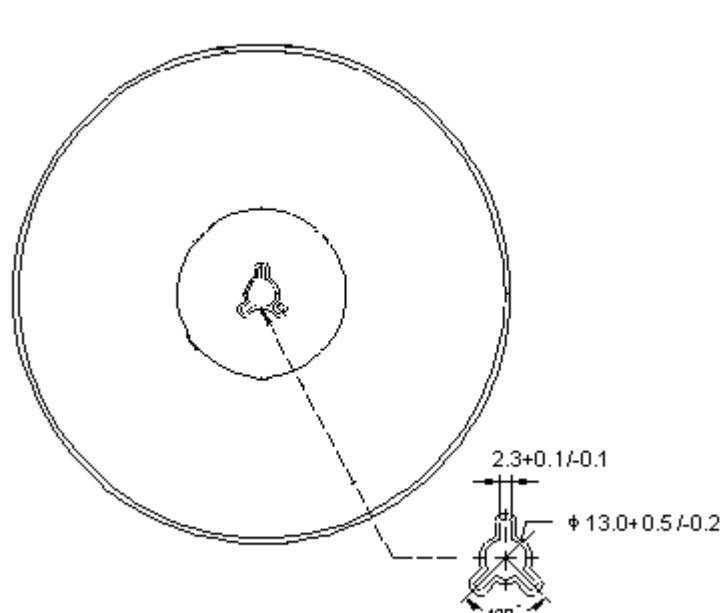


Recommended Soldering Footprint



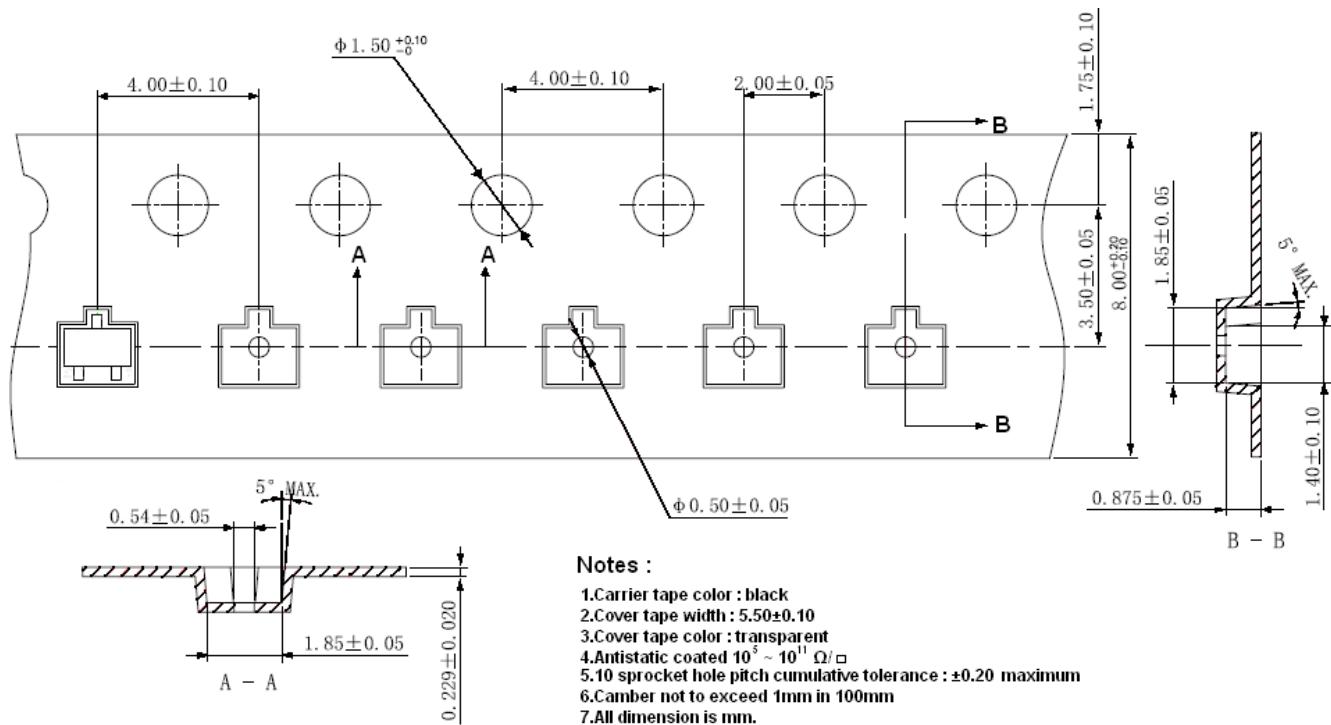
Dimensions in inches and (millimeters)

Reel Dimension

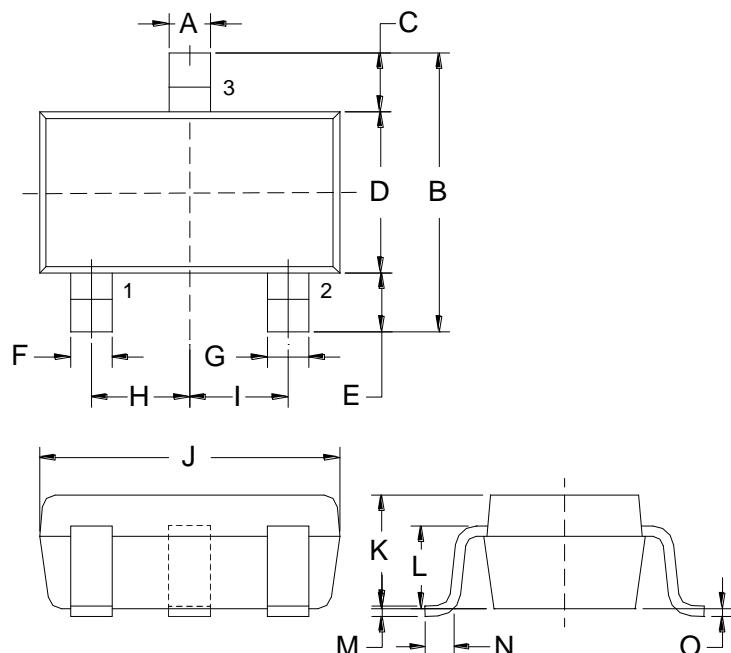


Unit: millimeter

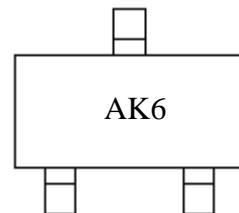
Carrier Tape Dimension



SOT-523 Dimension



Marking:



3-Lead SOT-523 Plastic Surface Mounted Package

Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0079	0.0157	0.20	0.40	I	*0.0197	-	*0.50	-
B	0.0591	0.0669	1.50	1.70	J	0.0610	0.0650	1.55	1.65
C	0.0118	0.0197	0.30	0.50	K	0.0276	0.0315	0.70	0.80
D	0.0295	0.0335	0.75	0.85	L	0.0224	0.0248	0.57	0.63
E	0.0118	0.0197	0.30	0.50	M	0.0020	0.0059	0.05	0.15
F	0.0039	0.0118	0.10	0.30	N	0.0039	0.0118	0.10	0.30
G	0.0039	0.0118	0.10	0.30	O	0	0.0031	0	0.08
H	*0.0197	-	*0.50	-					